

# **GBU8005 THRU GBU810**

### SINGLE PHASE8.0AMPS.GLASS PASSIVATED BRIDGE RECTIFIERS

### **FEATURE**

. UL Listed Under Recognized Component Index, File Number E338195

- . Glass passivated chip junctions
- . High case dielectric stength
- . Low Reverse Leakage Current
- . High surge current capability
- . Ideal for Printed Circuit Board Applications

#### **MECHANICAL DATA**

. Case: GBU

. Case Material: Molded Plastic.

UL Flammability Classification Rating 94V-0

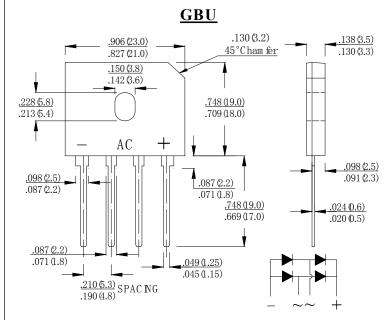
. Terminals: Pure tin plated, Lead free.

Leads solderable per MIL-STD-750, Method 2026.

. Polarity: Molded on Body

. Mounting: Through Hole for #6 Screw . Mounting Torque: 5.0 in-lbs Maximum

. Weight: 3.8 grams



Dimensions in inches and (millimeters)

# MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

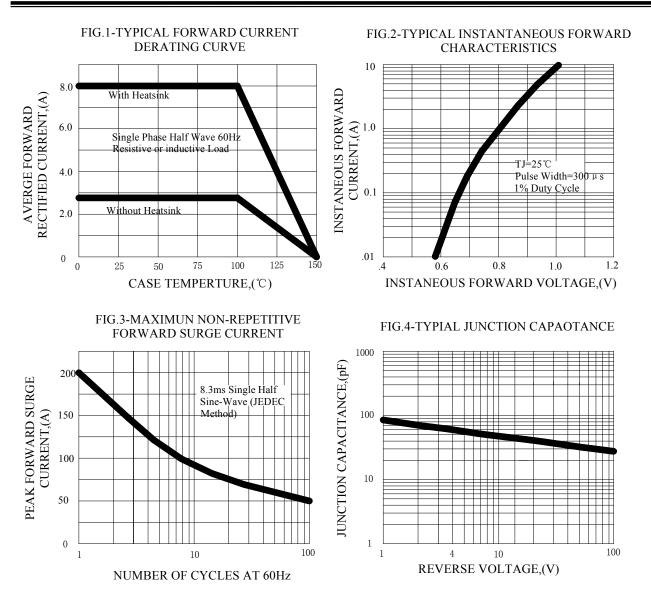
For capacitive load, derate current by 20%

Type Number	SYM BOL	GBU 8005	<b>GBU</b> 801	<b>GBU</b> 802	<b>GBU</b> 804	<b>GBU</b> 806	<b>GBU</b> 808	<b>GBU</b> 810	units
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{ m RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking Voltage	$V_{ m DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward (with heatsink Note	2)	8.0 2.8							A
Rectified Current @ T <sub>C</sub> =100°C(without heatsink	$I_{\text{F(AV)}}$								
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	$I_{ m FSM}$				200				A
Maximum Forward Voltage @ 8.0A DC Drop per element @ 4.0A DC	V <sub>E</sub>	1.1 1.0							V
Maximum DC Reverse Current $@T_J = 25^{\circ}\text{C}$ at rated DC blocking voltage $@T_J = 125^{\circ}\text{C}$	$I_{ m R}$	5.0 500.0							μΑ
I <sup>2</sup> t Rating for Fusing (t < 8.3ms)	<i>I</i> <sup>2</sup> t	166						A <sup>2</sup> Sec	
Typical Junction Capacitance (Note 1)	C <sub>J</sub>	60						pF	
Typical Thermal Resistance (Note 2)	R <sub>(JC)</sub>	2.2					°C/W		
Storage Temperature	T <sub>STG</sub>	-55 to +150						°C	
Operating Junction Temperature	$T_{ m J}$	-55 to +150						°C	

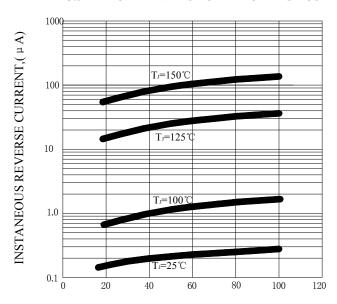
### Note:

- 1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 2.Device mounted on 100mm x 100mm x 1.6mm Cu Plate Heatsink.

# RATING AND CHARACTERISTIC CURVES (GBU8005 THRU GBU810)



### FIG.5-TYPICAL REVERSE CHARACTERISTICS



PERCENT OF RATED PEAK REVERSE VOLTAGE,(%)